



Development of the FEE-Powering: DC/DC

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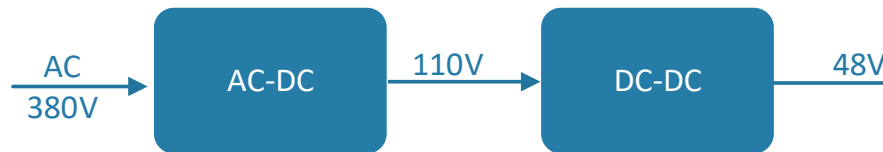
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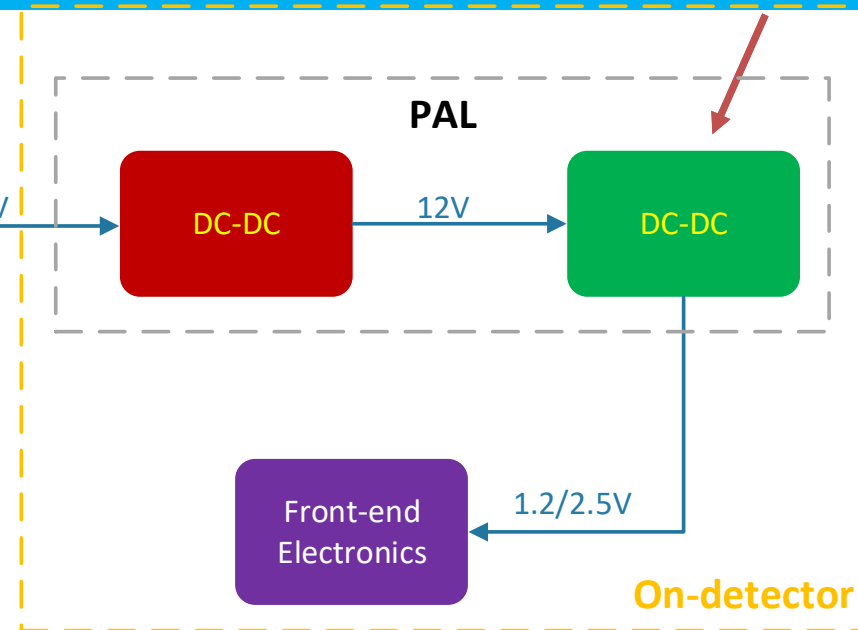
- Introduction
- Design of DC/DC buck converter
- Measurement results
- Summary and future work

Introduction

■ Power distribution system



- Compatible with traditional power system
- Good reliability
- Large area due to the air-core inductor
- Noise and EMI



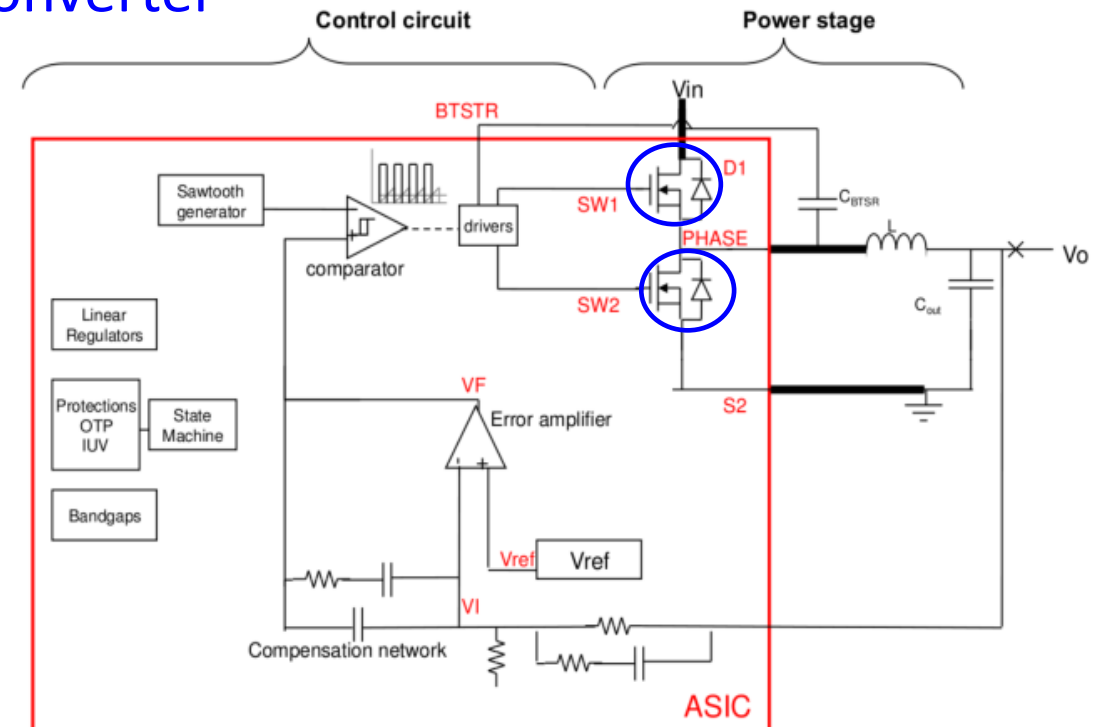
■ Harsh working environment

- High magnetic field (Up to 3T in CEPC)
- High level of radiation will be reached inside the detectors (0.6 Mrad/y)

Design of DC/DC buck converter

■ Design specification of the DC/DC converter

Parameter	Value
Input voltage	12-10 V
Output voltage	1.8/1.2 V
Output current	<10 A
Output ripple voltage	<10 mV
power efficiency	>80%
Power module size	<30x20x6.7mm ³
TID	0.6 Mrad/year
Magnetic field	3T
Switching frequency	1-3 MHz



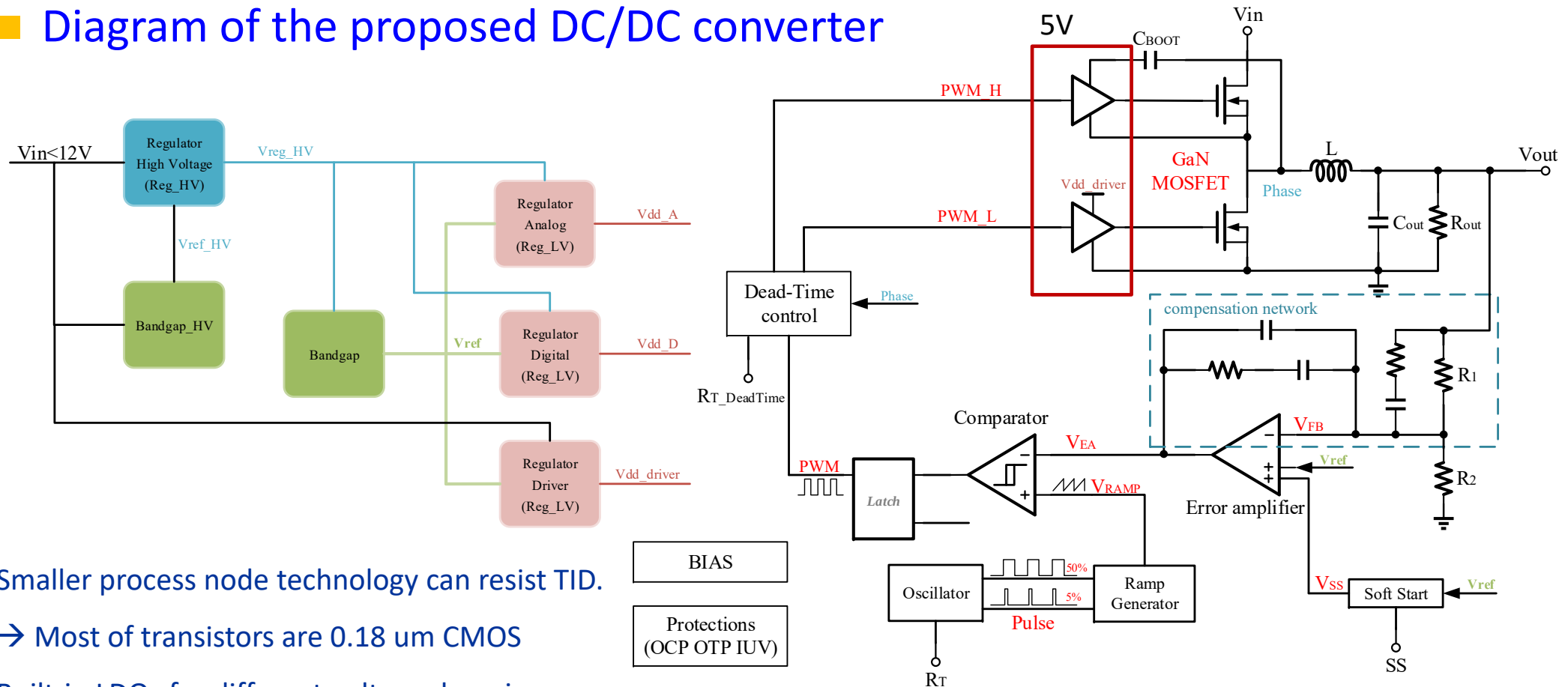
GaN power transistors are also considered to be used.

- fast switching speed
- low power loss
- high radiation tolerance
- low on-resistance

High current

Design of DC/DC buck converter

■ Diagram of the proposed DC/DC converter



- Smaller process node technology can resist TID.
 - ➔ Most of transistors are 0.18 um CMOS
- Built-in LDOs for different voltage domains

Controlling loop: Voltage mode PWM

Design of DC/DC buck converter

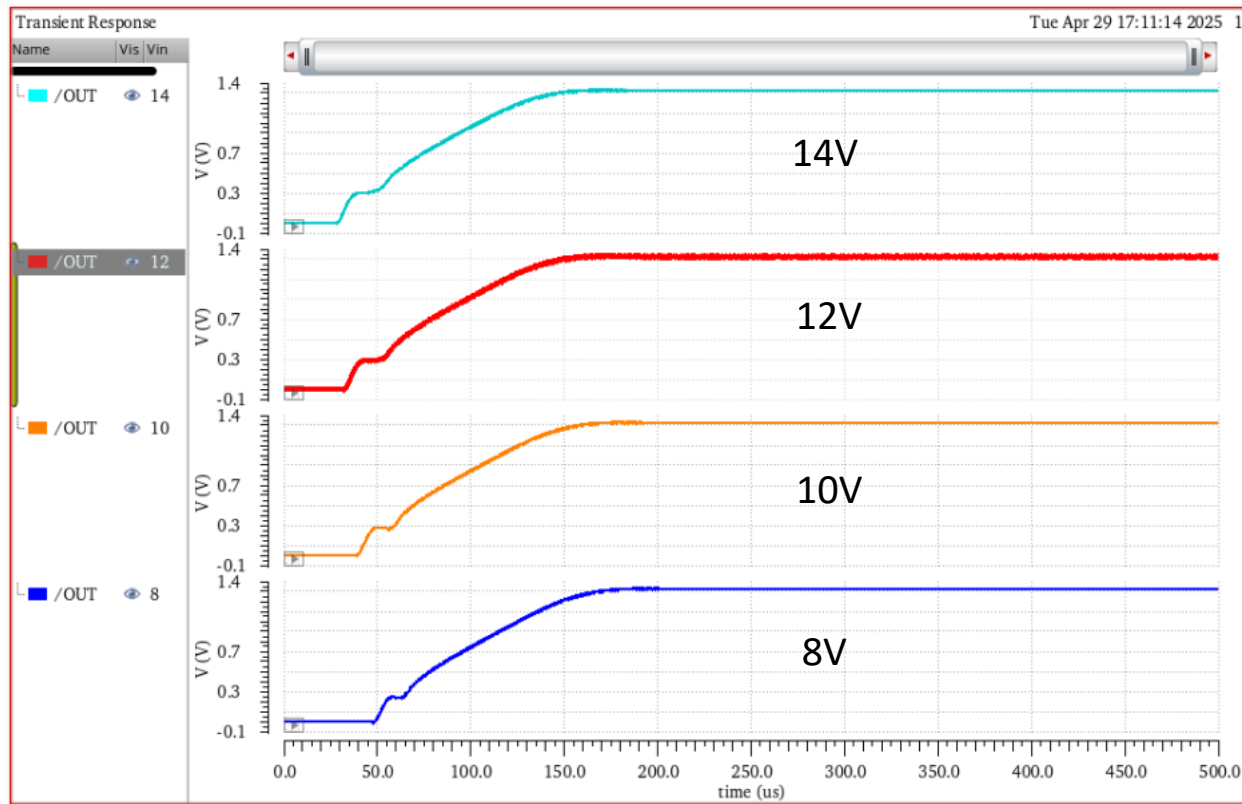
■ Simulated ripple voltage of the proposed DC/DC converter @ $I_o=10A$

Corner	VBG (mV)	RT(Ω)	f_{sw} (Hz)	Ripple current (A)	Vo(V)	Ripple voltage 1st(V)	Ripple voltage 2nd(V)	Efficiency (%)
SS	920	50k	3.72M	2.1	1.517	4.18m	425.6u	75.2
		100k	2.008M	3.6		9.618m	1.385m	81.6
		200k	1.085M	6.15		26.76m	4.594m	83.7
		400k	587.7K	11.2		92.3m	39.6m	84.3
		floating	1.892M	3.7		13.15m	835.6u	79.8
TT	835	50k	4.203M	1.75	1.332	3.785m	295.4u	72
		100k	2.281M	3.2		8.157m	627.1u	79
		200k	1.237M	5.9		20.93m	2.233m	83
		400k	672.4K	10.8		64.88m	17.87m	84.9
		floating	2.43M	3		7.417m	555.4u	78.4
FF	750	50k	4.762M	1.44	1.237	3.11m	277.3u	69.4
		100k	2.595M	2.63		6.427m	530.7u	77.3
		200k	1.415M	4.8		16.57m	2.433m	82.2
		400k	773.3K	8.8		45.47m	8.803m	84.9
		floating	3.164M	2.16		4.959m	435.7u	75.1

Ripple voltage can be decreased by increasing the switching frequency, while the power efficiency decreases.

Design of DC/DC buck converter

■ Start-up simulation @ VIN:14,12,10,8,6V



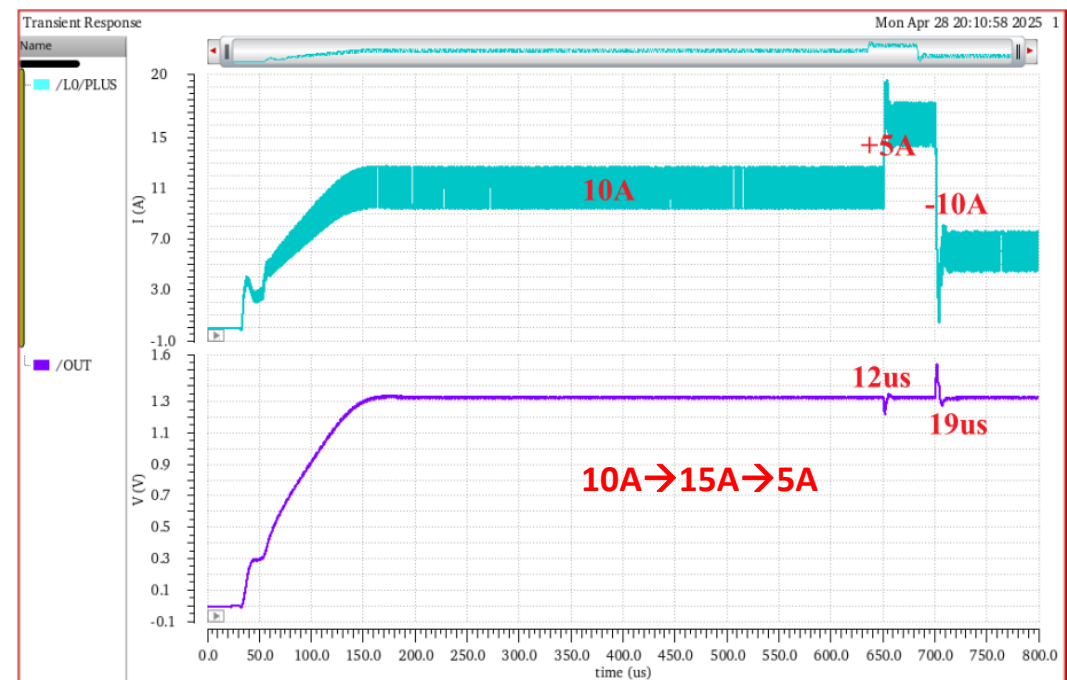
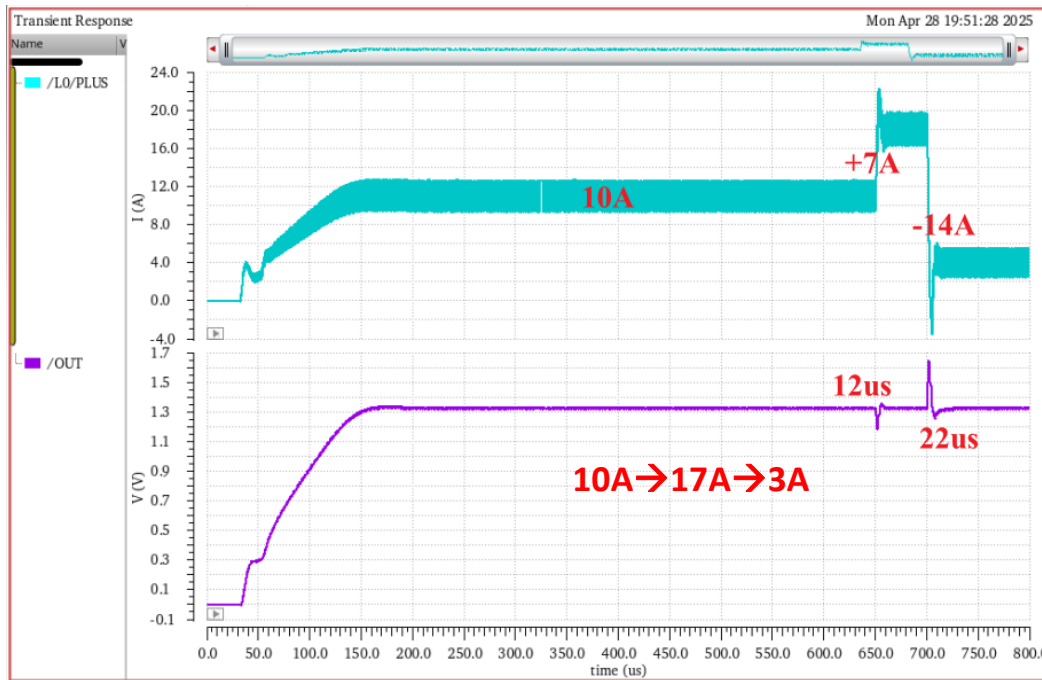
Vin (V)	14	12	10	8	6
Efficiency (%)	77.28	78.93	80.73	82.1	/
Switching Frequency	2.283 MHz				
Vo (V)	1.331				/
Vorip1st (mV)	8.365	8.159	8.03	7.121	/
Vorip2nd (uV)	686	705.1	840	314.5	/

The efficiency increases and ripple voltage decreases with input voltage decreasing, owing to the increase of duty cycle.

The converter can work well, except at vin of 6V. ←The under-voltage lockout (UVLO) works

Design of DC/DC buck converter

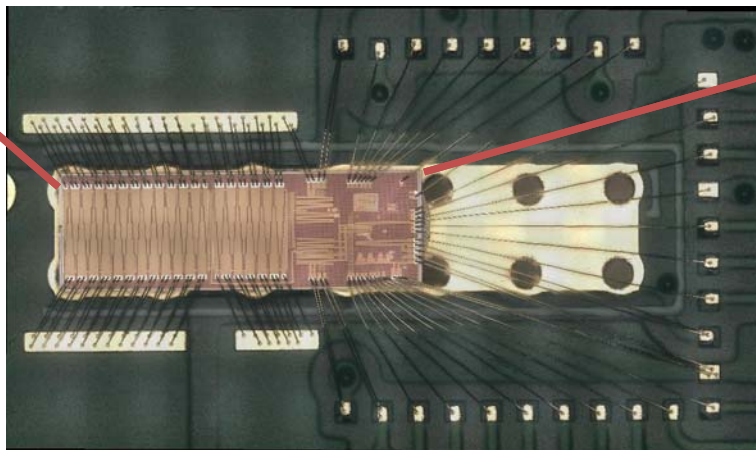
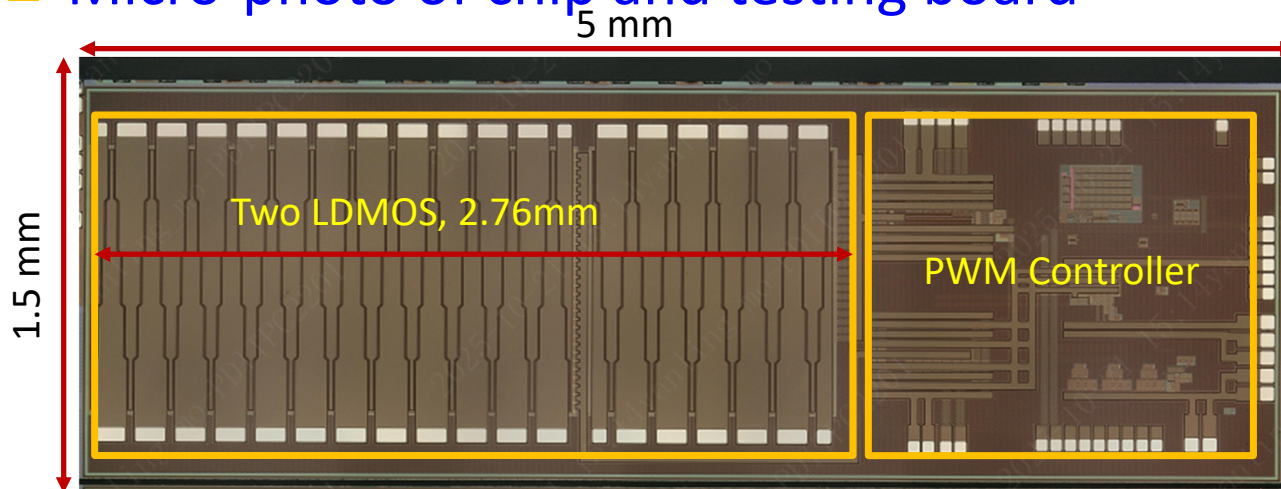
■ Transient response with load current step



- The output voltage can recover after 22us.
- No oscillation is observed.

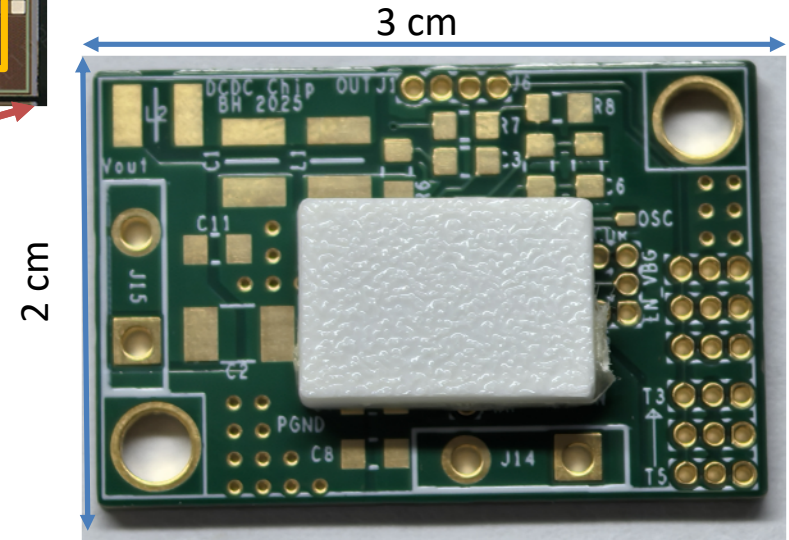
Primary measurement results

■ Micro-photo of chip and testing board



Assambled with Wire-bonding

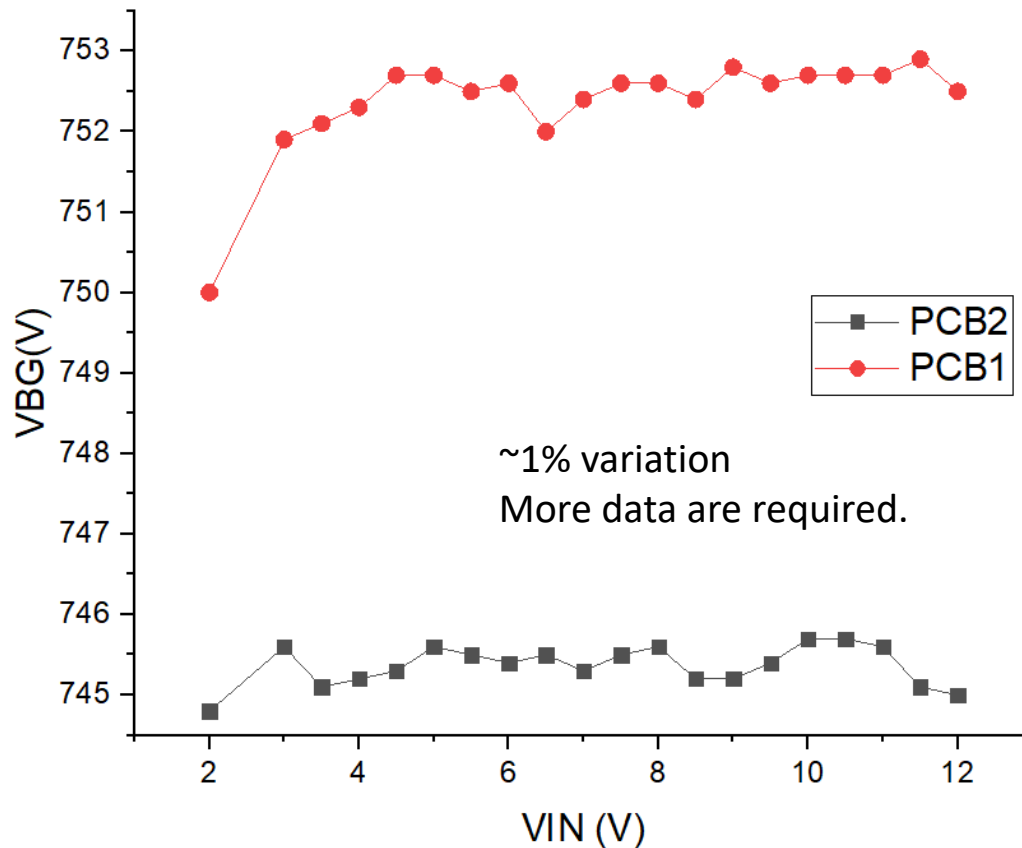
- 180nm BCD process
- 1.8V, 5V, 12V MOS devices
- Large area PADs → high current
- Fabricated at the end of October
- Measurement is ongoing



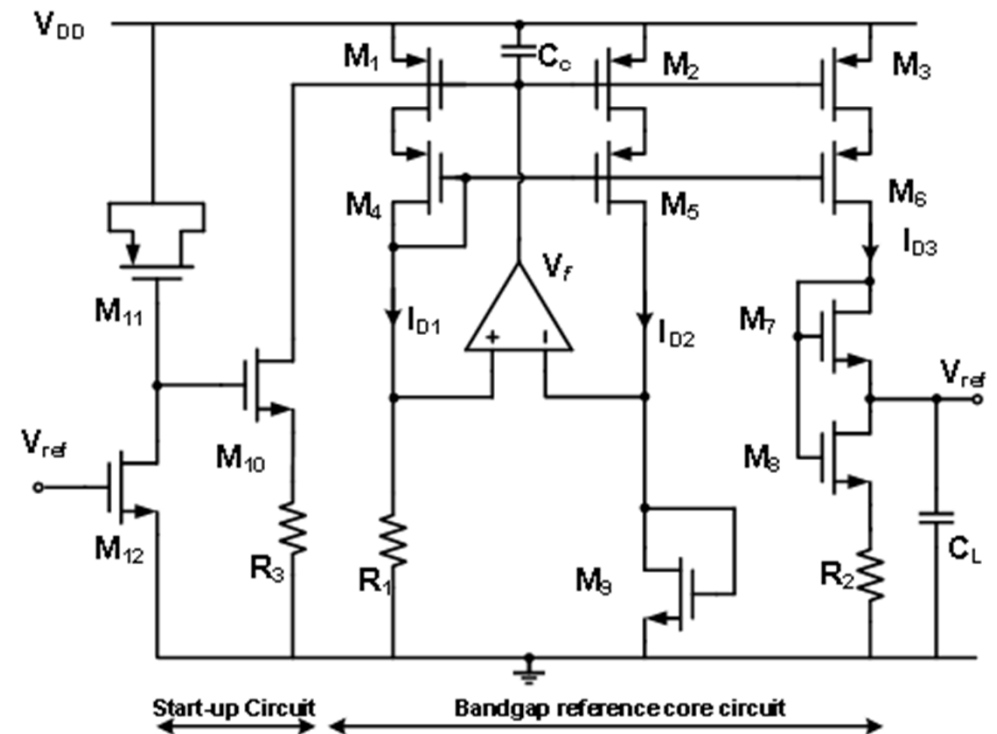
The photo of the testing board 9

Primary measurement results

■ Bandgap Voltage VS VIN



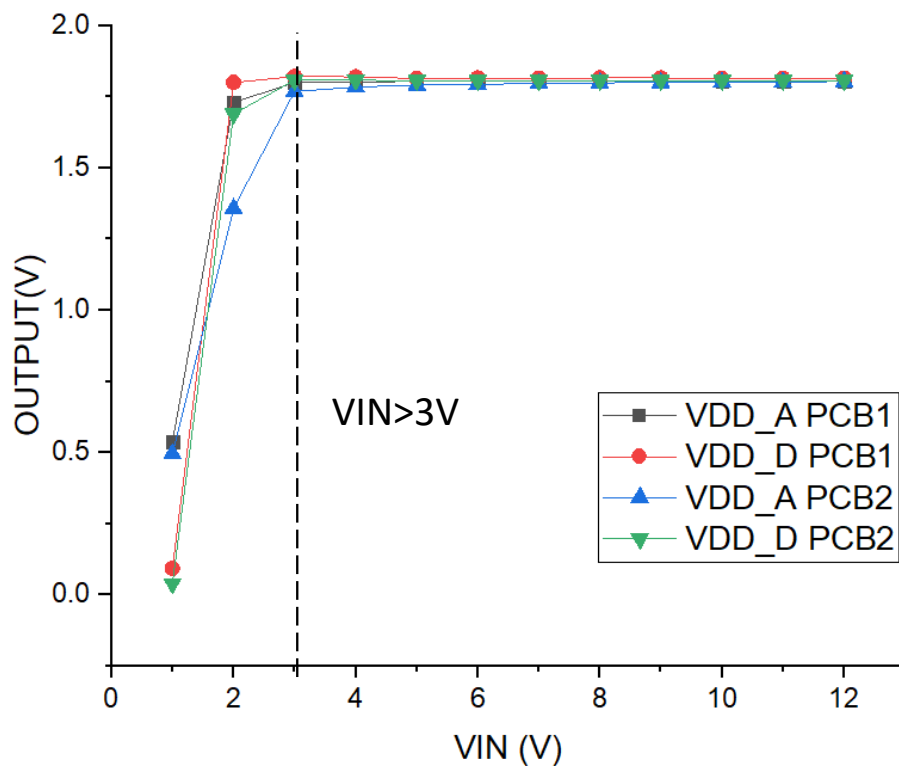
The full CMOS bandgap output can be unvaried with VIN



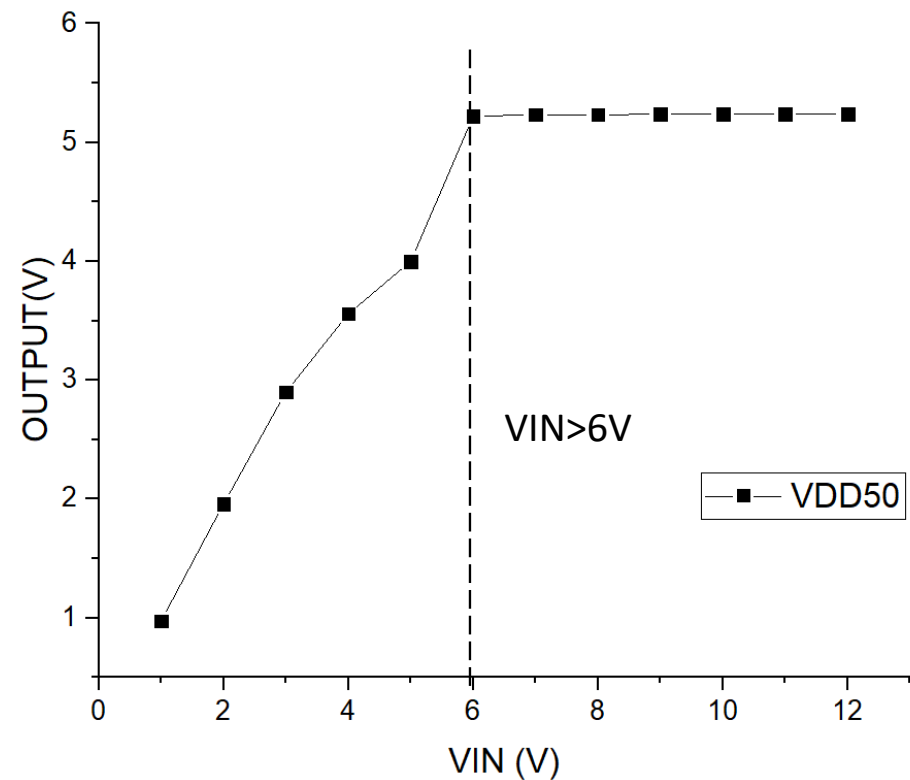
Schematic of the bandgap

Primary measurement results

■ Measurement results of the built-in regulators



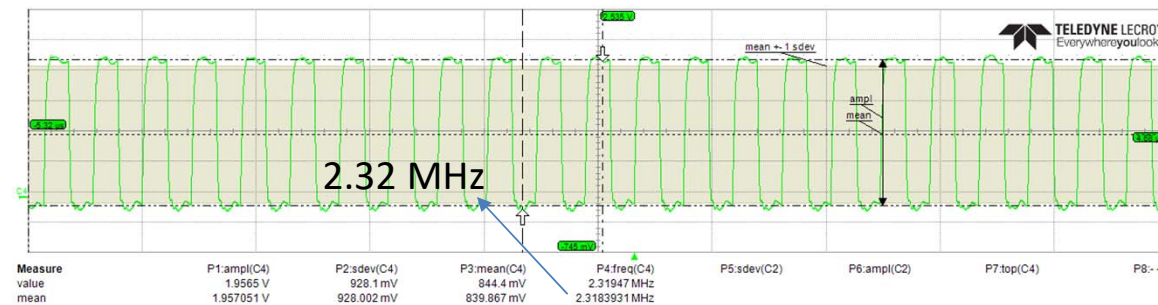
Supply analogue/digital power for controller (1.8V)



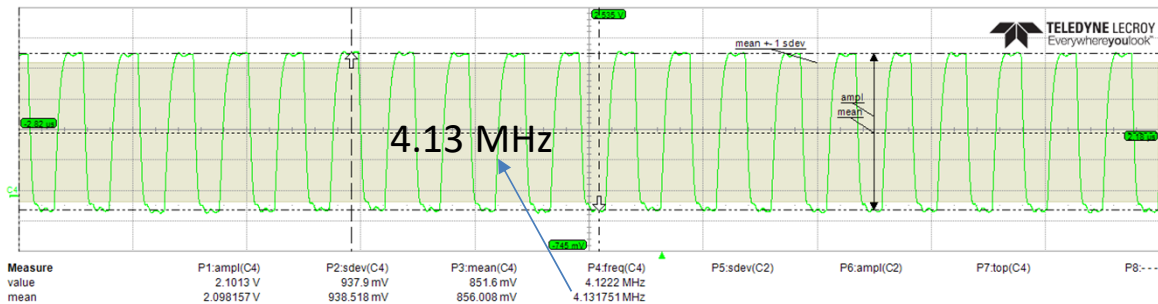
Supply power for the LDMOS driver (5V)

Layout and measurement results

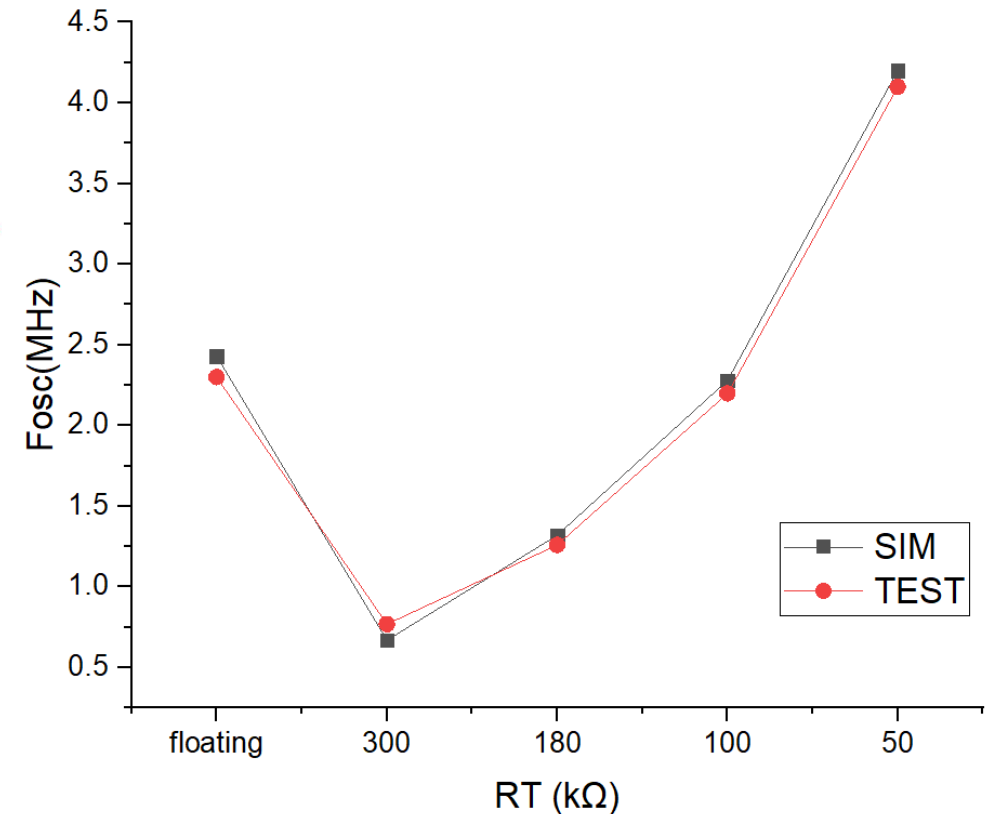
Measured frequency of oscillator



Works with internal current source, when RT is floating.



Works with external current source, when RT is 50kΩ



- Frequency changes linearly with the value of RT(0.5-4MHz)
- Test results are consistent with simulation results

Summary and working plan

■ Conclusion

- ❑ A radiation tolerance 12V-1.2V DC/DC converter has been designed and fabricated.
- ❑ Simulation results demonstrate low ripple voltage can be achieved by higher switching frequency and larger inductor.
- ❑ Measured results demonstrate the built-in bandgap, regulators and oscillator can work well.

■ Future work

- ❑ Continue to test the prototype chip (with GaN power transistors)
- ❑ The irradiation experiment will be completed.



Thanks for your attention!

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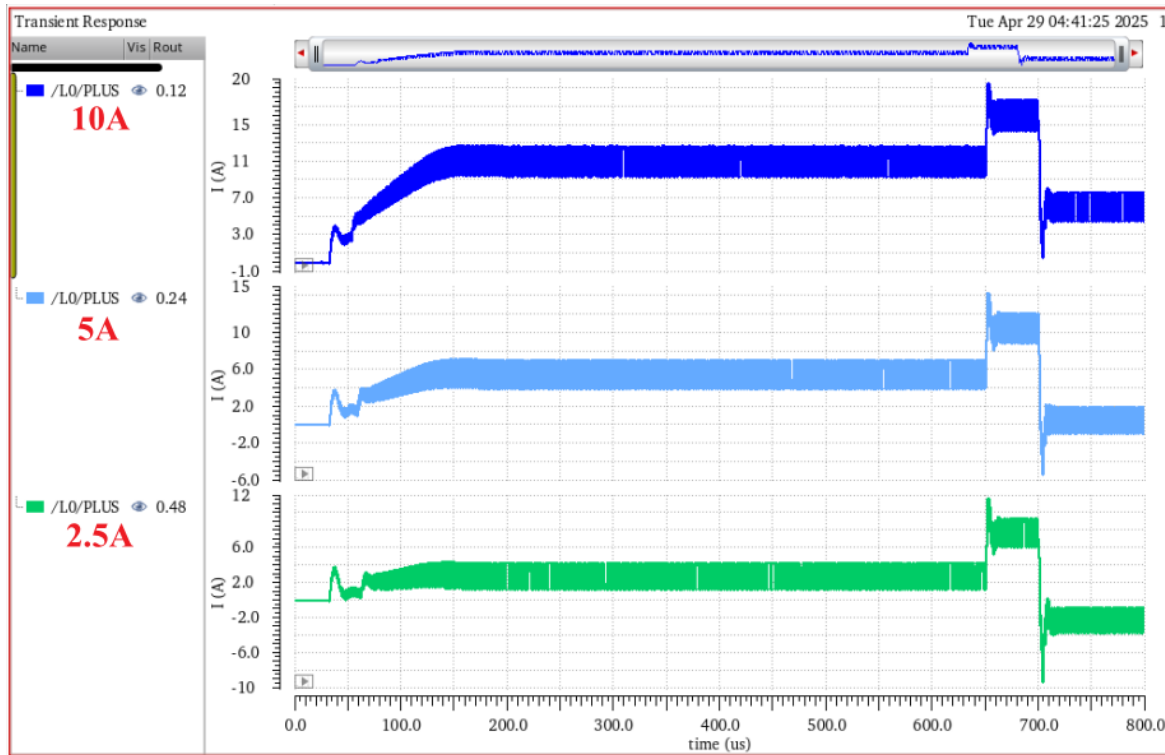


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Design of DC/DC buck converter

不同负载情况启动过程仿真



Load current(A)	10	5	3.3	2.5
Efficiency(%)	83.14	83.15	83.16	/
Frequency(Hz)	2.283M			
Output voltage(V)	1.331			
Ripple voltage 1st(V)	8.594m	7.845m	7.504m	7.54m
Ripple voltage 2nd(V)	1.173m	705.1u	354.2u	574.4u

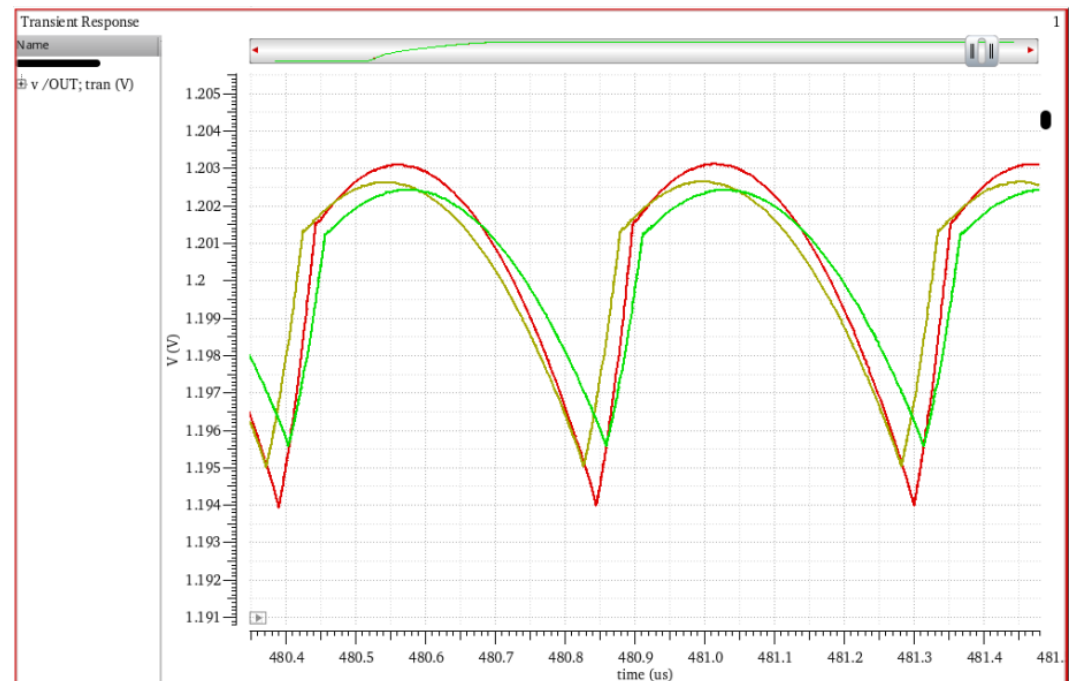
➤ 负载为10A、5A、2.5A情况下，电路均可以正常启动，输出稳定的电压信号

Design of DC/DC buck converter

■ 电压纹波受电感值影响仿真

- ①受振荡器频率控制，芯片工作频率保持不变
- ②输出纹波与感值成反比
- ③不同电感值下，输出信号有一定的相位差

电感感值(nH)	150	180	200
电源效率(%)	83.14	83.15	83.16
工作频率(Hz)	2.162M	2.164M	2.16M
第一级输出纹波(V)	9.477m	7.859m	7.046m
第二级输出纹波(V)	452.9u	442.8u	382.1u



Design of DC/DC buck converter

Simulation Results

/	Corner	$f_{sw}(Hz)$	VBG(V)	Output voltage (V)	Ripple current (A)	Ripple voltage(V)		Efficiency(%)
						(1st)	(2nd)	
PRE-SIM	SS	2.008M	920	1.517	3.6	9.618m	1.385m	81.6
	TT	2.281M	835	1.332	3.2	8.157m	627.1u	79.4
	FF	2.595M	750	1.237	2.63	6.427m	530.7u	77.4
POST-SIM	SS	1.979M	761	1.179	3.19	8.397m	631.8u	79.0
	TT	2.283M	765	1.127	2.83	6.895m	359.5u	80.1
	FF	2.696	763	1.261	2.47	5.715m	306.2u	79.6

对各工艺角下带隙进行了修调：

Corners	Nominal	ss	ff	tt
Temperature		125	-40	27
Design Variables				
T5		1.8	0	1.8
T4		1.8	0	0
T3		1.8	0	0
T2		0	0	0
T1		1.8	0	0
T0		0	1.8	0

不同工艺角下电路启动过程后仿真：

